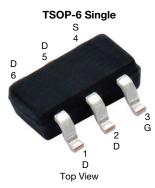
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Vishay Siliconix

Automotive P-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V _{DS} (V)	-60
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	0.095
$R_{DS(on)}$ (Ω) at V_{GS} = -4.5 V	0.135
I _D (A)	-5.3
Configuration	Single

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



FREE

(1, 2, 5, 6) D (3) G (4) S

P-Channel MOSFET

Marking Code: 9Q

ORDERING INFORMATION			
Package	TSOP-6		
Lead (Pb)-free and halogen-free	SQ3427CEV (for detailed order number please see <u>www.vishay.com/doc?79771</u>)		

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage Gate-Source Voltage		V _{DS}	-60	N/		
		V _{GS}	± 20	V		
Continuous Drain Current	T _C = 25 °C	- I _D -	-5.3			
	T _C = 125 °C		-3			
Continuous Source Current (Diode Conduction)		I _S	-6.3	А		
Pulsed Drain Current ^a		I _{DM}	-21			
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	-21			
Single Pulse Avalanche Energy		E _{AS}	22	mJ		
Maximum Power Dissipation	T _C = 25 °C	P _D	5	W		
	T _C = 125 °C		1.6	vv		
Operating Junction and Storage Temperature F	Range	TJ, T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient PCB Mount ^b		R _{thJA}	110	°C/W	
Junction-to-Foot (Drain)		R _{thJF}	30	0/10	

Notes

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. When mounted on 1" square PCB (FR4 material).

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	•	•						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = -250 μA		-60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		-2	-2.5		
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20 V$	-		± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = -60 V	-	-	-1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 125 °C	-	-	-50	μA	
-		$V_{GS} = 0 V$	V _{DS} = -60 V, T _J = 175 °C	-	-	-150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-10	-	-	Α	
		V _{GS} = -10 V	I _D = -4.5 A	-	0.079	0.095		
	R _{DS(on)}	$V_{GS} = -10 V$	I _D = -4.5 A, T _J = 125 °C	-	-	0.148	Ω	
Drain-Source On-State Resistance ^a		V _{GS} = -10 V	I _D = -4.5 A, T _J = 175 °C	-	-	0.178		
		V _{GS} = -4.5 V	I _D = -3.5 A	-	0.112	0.135		
Forward Transconductance ^a	g _{fs}	V _{DS} :	= -15 V, I _D = -4 A	-	9	-	S	
Dynamic ^b					•			
Input Capacitance	C _{iss}		V _{DS} = -30 V, f = 1 MHz	-	726	1000	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	91	120		
Reverse Transfer Capacitance	C _{rss}			-	56	80		
Total Gate Charge ^c	Q _g			-	16.9	22	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = -10 V	V _{DS} = -30 V, I _D = -5 A	-	2.9	-		
Gate-Drain Charge ^c	Q _{qd}				4.1	-		
Gate Resistance	R _g		f = 1 MHz		5	7.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	8	12	ns	
Rise Time ^c	t _r	- Voo :	$V_{DD} = -30 \text{ V}, \text{ R}_{1} = 6 \Omega$		24	35		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ -5 Å, V_{GEN} = -10 V, R_g = 1 Ω		-	25	38		
Fall Time ^c	t _f			-	33	50		
Source-Drain Diode Ratings and Characte	ristics ^b				•			
Pulsed Current ^a	I _{SM}			-	-	-21	Α	
Forward Voltage	V _{SD}	I _F = -1.6 A, V _{GS} = 0 V		-	-0.8	-1.2	V	
Body diode reverse recovery time	t _{rr}	I _F = -1.7 A, di/dt = 100 A/μs		-	23	46	ns	
Body diode reverse recovery charge	Q _{rr}			-	27	54	nC	
Reverse recovery fall time	ta			-	20	-		
Reverse recovery rise time	t _b			-	3	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.86	-	А	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

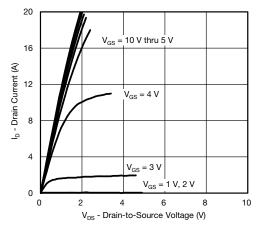
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

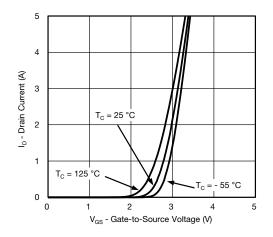


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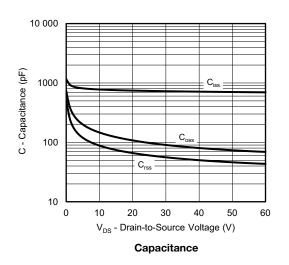
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

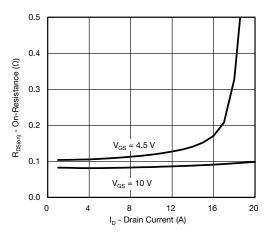


Output Characteristics

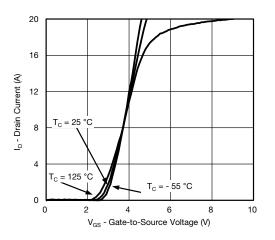


Transfer Characteristics

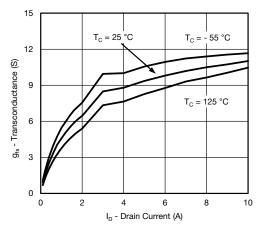




On-Resistance vs. Drain Current and Gate Voltage



Transfer Characteristics



Transconductance

S23-0708-Rev. B, 11-Sep-2023

3

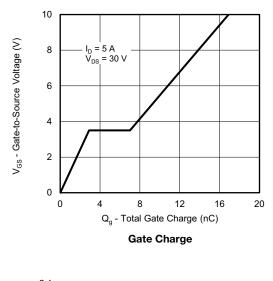
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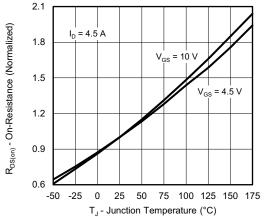
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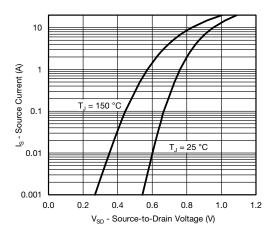
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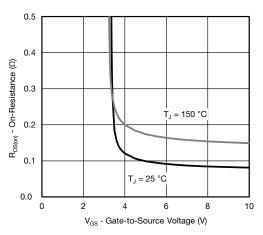




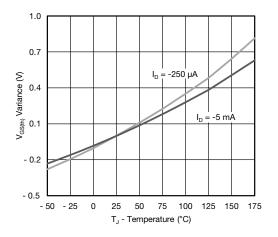
On-Resistance vs. Junction Temperature



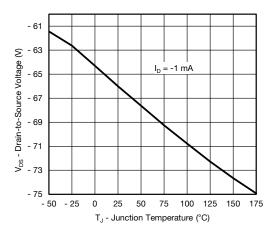
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Drain-to-Source Voltage vs. Junction Temperature

S23-0708-Rev. B, 11-Sep-2023

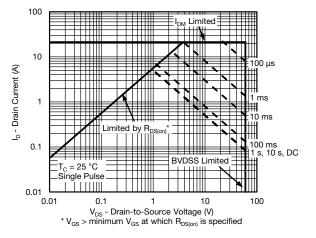
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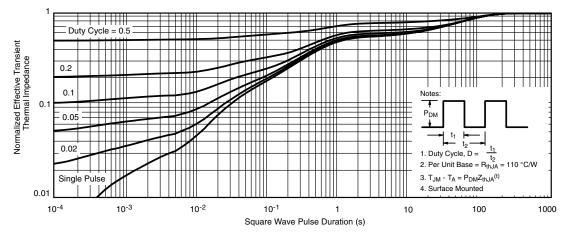


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient

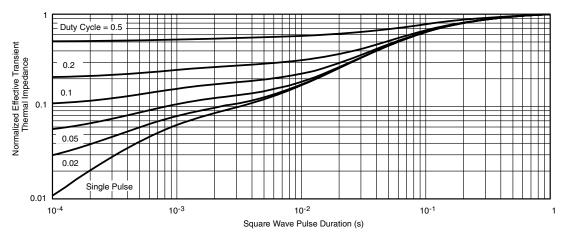


Normalized Thermal Transient Impedance, Junction-to-Ambient



Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62369.



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